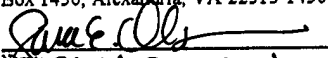


**METHODS FOR FORMING CONDUCTIVE STRUCTURES  
AND STRUCTURES REGARDING SAME**

**Abstract of the Invention**

5       A method for forming a metal/metal oxide structure that includes forming metal  
oxide regions, e.g., ruthenium oxide regions, at grain boundaries of a metal layer, e.g.,  
platinum. Preferably, the metal oxide regions are formed by diffusion of oxygen  
through grain boundaries of the metal layer, e.g., platinum, to oxidize a metal layer  
thereon, e.g., ruthenium layer. The structure is particularly advantageous for use in  
capacitor structures and memory devices, such as dynamic random access memory  
10       (DRAM) devices.

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| <p>"Express Mail" mailing label number <u>EV 073735351 US</u></p> <p>Date of Deposit September <u>24</u>, 2003</p> <p>I hereby certify that the Transmittal Letter and the paper(s) and/or fee(s), as described hereinabove, are being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 C.F.R. 1.10 on the date indicated above and is addressed to the Assistant Commissioner for Patents, Mail Stop PATENT APPLICATION, P. O. Box 1450, Alexandria, VA 22313-1450.</p> <p><br/>Name: <u>SARA E. OLSON</u></p> |
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